PHD13003C

NPN power transistor with integrated diode Rev. 01 — 29 July 2010

Product data sheet

Product profile 1.

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a SOT54 plastic package

1.2 Features and benefits

- Fast switching
- High typical DC current gain
- High voltage capability
- Integrated anti-parallel E-C diode

1.3 Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- Off-line self-oscillating power supplies (SOPS) for battery charging

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{C}	collector current	DC	-	-	1.5	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; see <u>Figure 1</u>	-	-	2.1	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	700	V
Static chara	Static characteristics					
h _{FE}	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V};$ $T_{j} = 25 \text{ °C}$	8	17	25	



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector		c L
3	E	emitter	321	B
			SOT54 (TO-92)	

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PHD13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54	

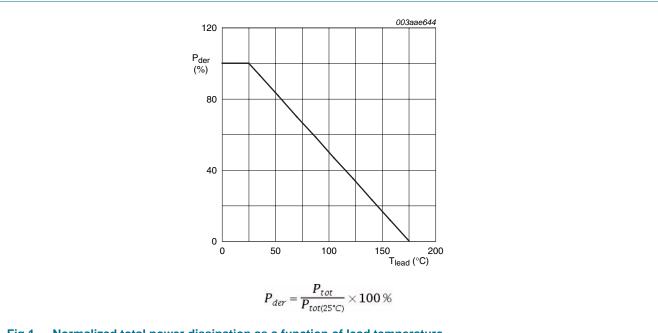
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
I _C	collector current	DC	-	1.5	Α
I _{CM}	peak collector current		-	3	Α
I _B	base current	DC	-	0.75	Α
I _{BM}	peak base current		-	1.5	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; see <u>Figure 1</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V _{EBO}	emitter-base voltage	$I_C = 0 A$; $I(Emitter) = 10 mA$	-	9	V

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Normalized total power dissipation as a function of lead temperature

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Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	see Figure 2	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W

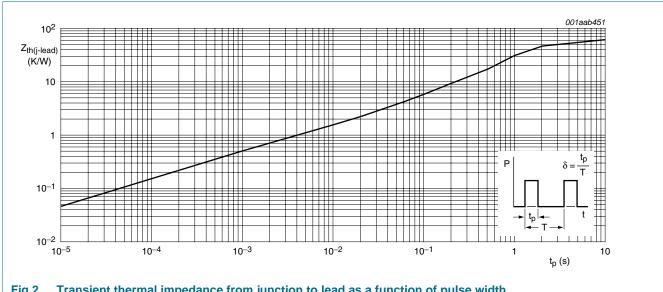


Fig 2. Transient thermal impedance from junction to lead as a function of pulse width

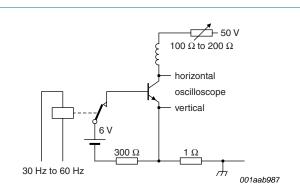
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6. Characteristics

Table 6. Characteristics

Table 0.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V	-	-	1	mΑ
	current	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	-	5	mΑ
I _{CEO}	collector-emitter cut-off current	V_{CE} = 400 V; I_{B} = 0 A; T_{lead} = 25 °C	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}$; $I_C = 1 \text{ mA}$; $L_C = 25 \text{ mH}$; $T_{lead} = 25 ^{\circ}\text{C}$; see <u>Figure 3</u> ; see <u>Figure 4</u>	400	-	-	V
V _{CEsat}	collector-emitter	$I_C = 0.5 \text{ A}; I_B = 0.1 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	0.5	V
	saturation voltage	$I_C = 1 \text{ A}; I_B = 0.25 \text{ A}; T_{lead} = 25 \text{ °C}$	-	-	1	V
		$I_C = 1.5 \text{ A}; I_B = 0.5 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1.5	V
V_{BEsat}	base-emitter saturation	$I_C = 0.5 \text{ A}; I_B = 0.1 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1	V
	voltage	$I_C = 1 \text{ A}; I_B = 0.25 \text{ A}; T_{lead} = 25 \text{ °C}$	-	-	1.2	V
V _F	forward voltage	I _F = 0.5 A; T _j = 25 °C	-	-	1.5	V
h _{FE}	DC current gain	$I_C = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_j = 25 \text{ °C}$	8	17	25	
		I _C = 1 A; V _{CE} = 2 V; T _j = 25 °C	5	9	15	
Dynamic	characteristics					
t _{on} turn-on time		$I_C = 1 \text{ A}$; $I_{Bon} = 0.2 \text{ A}$; $I_{Boff} = -0.2 \text{ A}$;	-	-	1	μs
t _s	storage time	R_L = 75 Ω; T_{lead} = 25 °C; resistive load; see <u>Figure 5</u> ; see <u>Figure 6</u>	-	-	4	μs
		I_C = 1 A; I_{Bon} = 0.2 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	0.8	-	μs
t _f	fall time	$I_C = 1$ A; $I_{Bon} = 0.2$ A; $I_{Boff} = -0.2$ A; $R_L = 75 \Omega$; $T_{lead} = 25$ °C; resistive load; see <u>Figure 5</u> ; see <u>Figure 6</u>	-	-	0.7	μs
		I_C = 0.5 A; I_{Bon} = 0.1 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	0.1	-	μs

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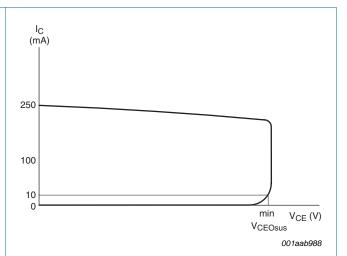
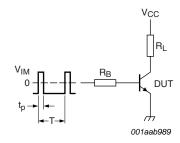
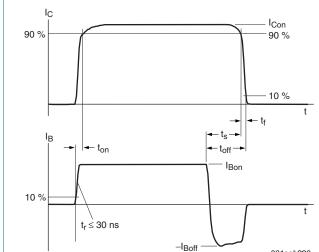


Fig 3. Test circuit for collector-emitter sustaining

Fig 4. Oscilloscope display for collector-emitter sustaining voltage test waveform





 $V_{IM}=-6$ to +8 V; $V_{CC}=250$ V; $t_p=20$ μs ; $\pmb{\delta}=\frac{t_p}{T}=0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 6. Switching times waveforms for resistive load

Fig 5. Test circuit for resistive load switching

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Switching times waveforms for inductive load

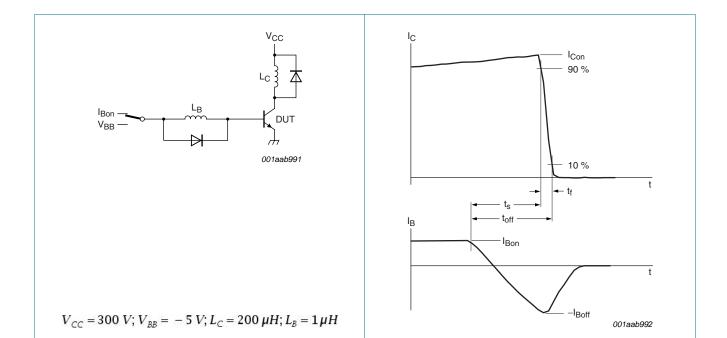


Fig 8.

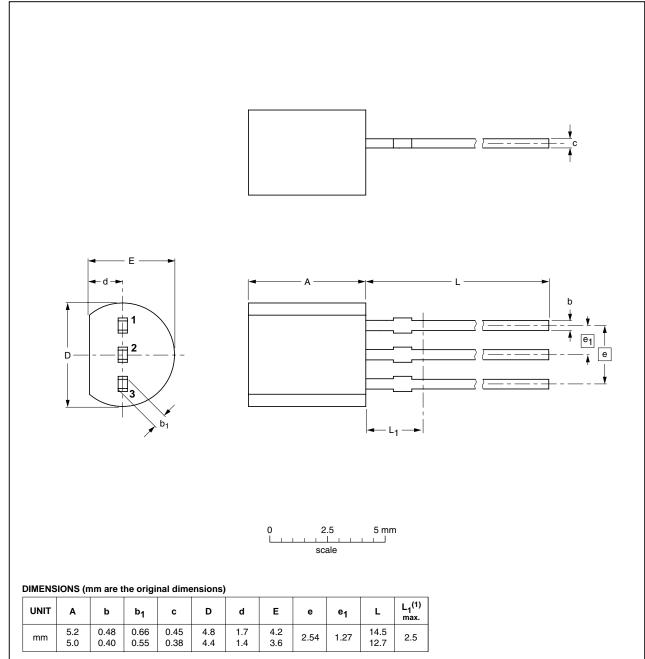
Fig 7. Test circuit for inductive load switching

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7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A		04-06-28 04-11-16

Fig 9. Package outline SOT54 (TO-92)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD13003C v.1	20100729	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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